HVM132WK

Silicon Epitaxial Planar Pin Diode for Antenna Switching

HITACHI

ADE-208-319B (Z)
Rev. 2
Jan. 1996

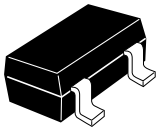
Features

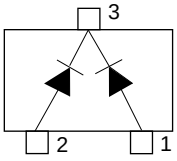
- Low capacitance.(C = 0.5pFmax)
- Low forward resistance. (r_f = 2.0Ωmax)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM132WK	P4	MPAK

Outline





(Top View)

1 Anode
2 Anode
3 Cathode

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F*	100	mA
Power dissipation	Pd*	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

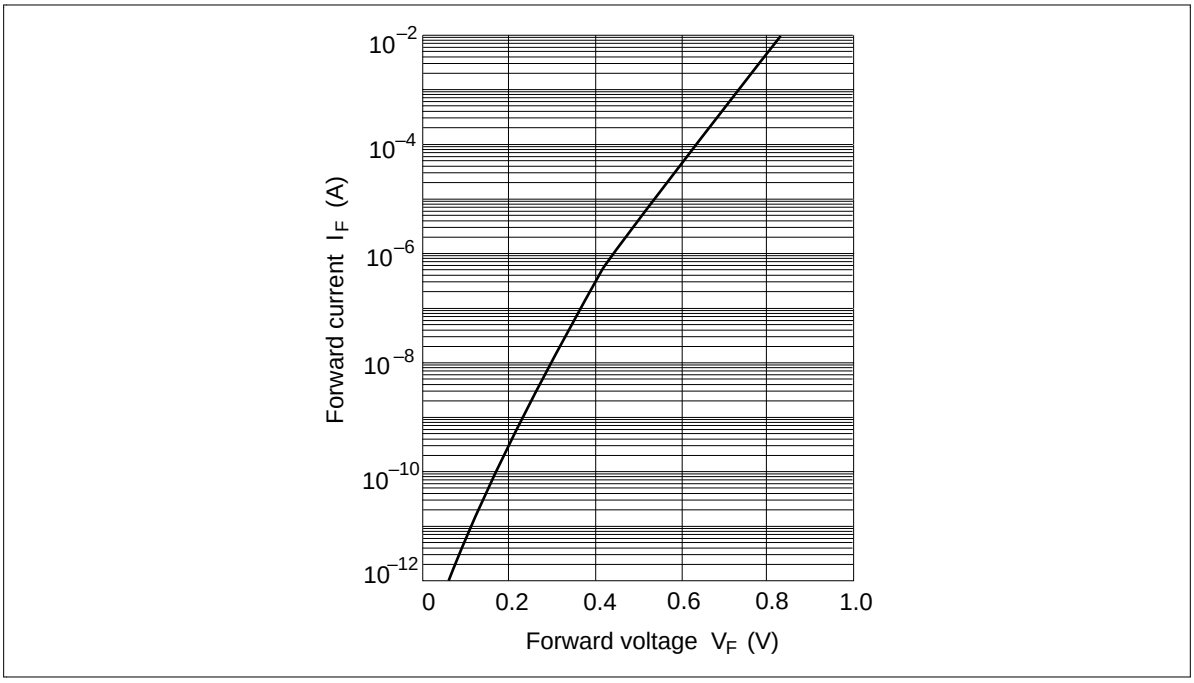
Note: Two device total

Electrical Characteristics (Ta = 25°C)*

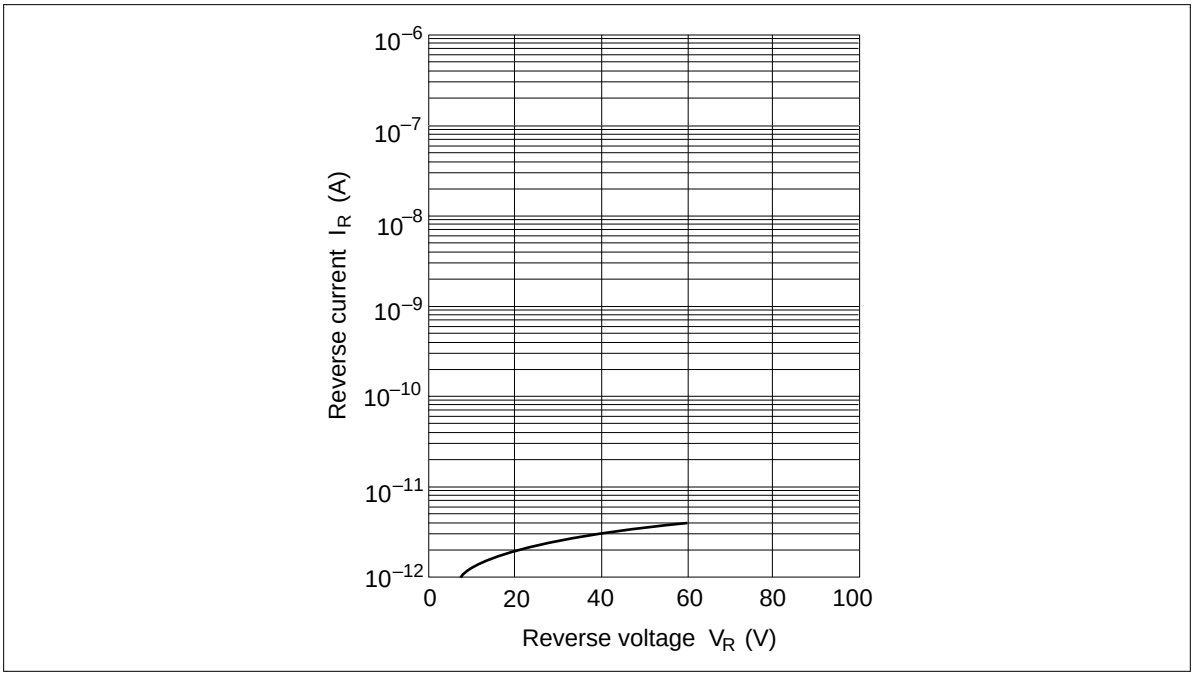
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	I_F = 10mA
Reverse current	I_R	—	—	0.1	µA	V_R = 60V
Capacitance	C	—	—	0.5	pF	V_R = 1V, f = 1MHz
Forward resistance	r_f	—	—	2.0	Ω	I_F = 10mA, f = 100MHz

Note: Do not guarantee electrical characteristics when forward bias between (1) - (3) or (2) - (3) and reverse bias between (2) - (3) or (1) - (3) at the same time and vice versa.

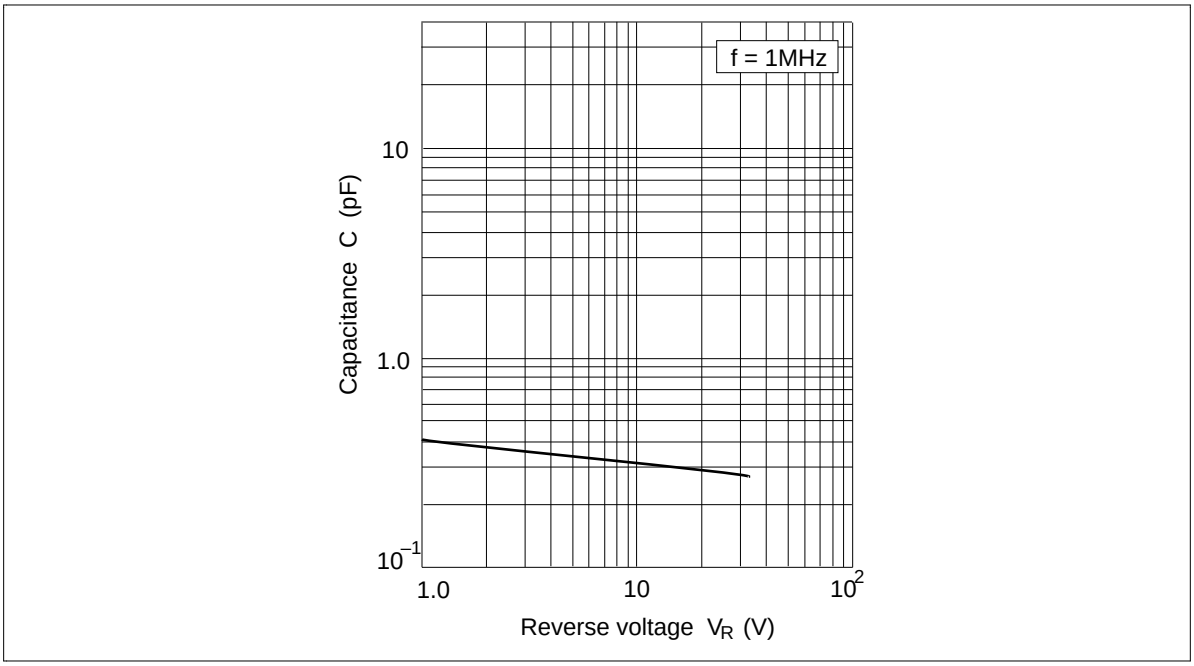
Forward current Vs. Forward voltage



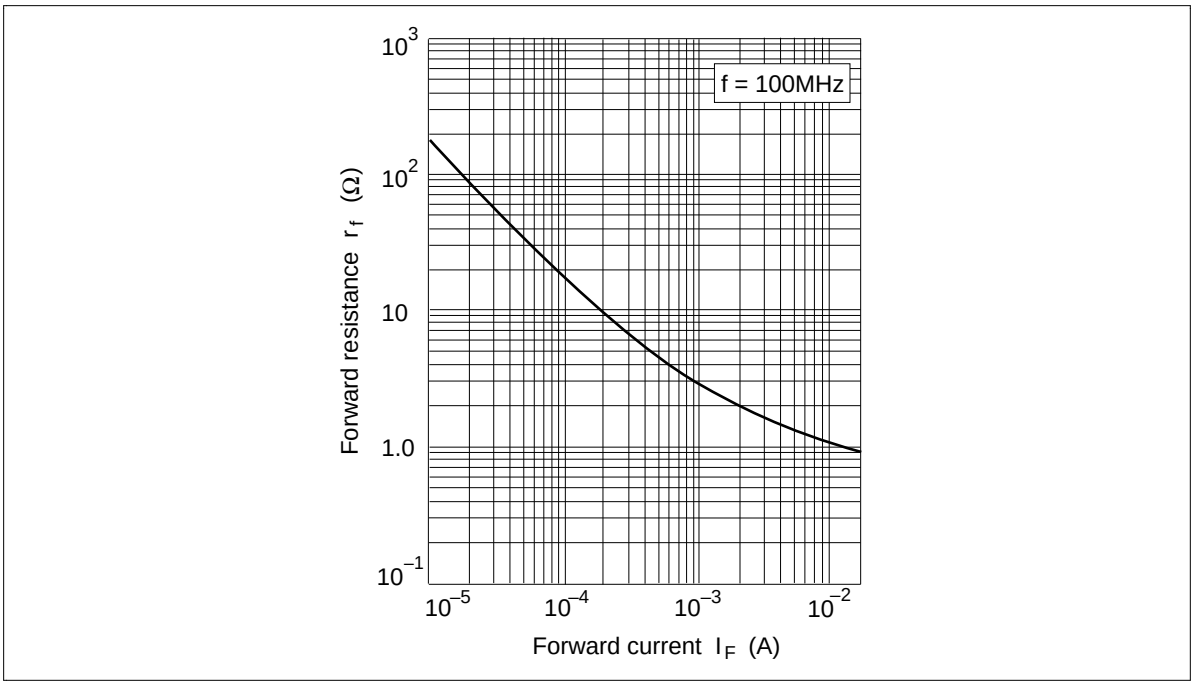
Reverse current Vs. Reverse voltage



Capacitance Vs. Reverse voltage

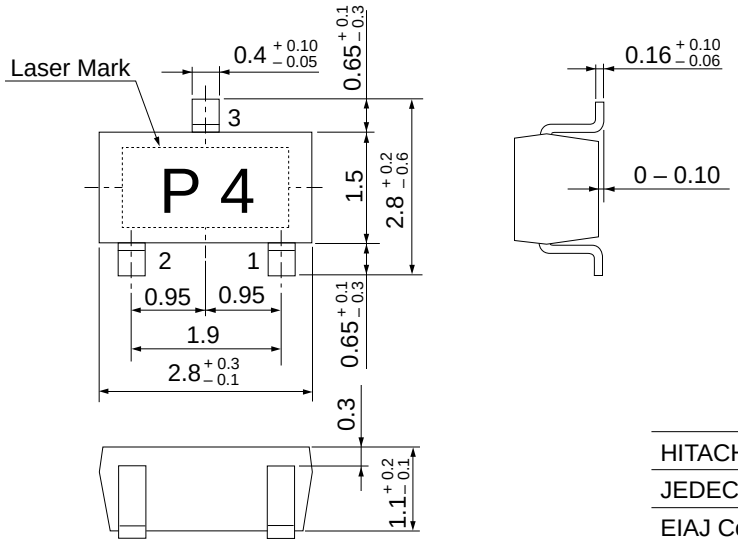


Forward resistance Vs. Forward current



Package Dimensions

Unit: mm



1 Anode
2 Anode
3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011